

REMARKS

Claims 1, 5, 6, 12 and 15-21 are pending in this application. By this Amendment, claims 1, 5, 6, 12 and 15-18 are amended. These amendments are supported by Applicants' specification at least at, page 5, lines 7-20; page 7, line 24 - page 8, line 6; page 17, line 10 - page 18, line 10; page 27, line 20 - page 28, line 10; and page 31, line 22 - page 32, line 20. Claims 19-21 are added. No new matter is added. Claims 2-4, 7-11, 13 and 14 are canceled without prejudice to, or disclaimer of, the subject matter that each of these claims recites. Claims 15-18 are withdrawn from consideration as drawn to a non-elected group of claims. Reconsideration of the application based on the above amendments and the following remarks is respectfully requested.

Withdrawn claims 15 and 17 are amended to recite all of the combination of features recited in claim 1 as method steps. Withdrawn claims 16 and 18 are amended to recite all of the combination of features recited in claim 6 as method steps. At least for these reasons, and upon finding claims 1 and 6 allowable for the reasons indicated below rejoinder and allowance of claims 15-18 are respectfully requested.

The Office Action rejects claims 6 and 14 under 35 U.S.C. §102(b) as being anticipated by JP-A-10-242254 to Satoshi. This rejection is respectfully traversed.

Claim 6 recites, among other features, the supporting portion is formed from a silicon plate-like member, a thickness of the supporting portion is not less than twice a thickness of the substrate and not more than 10 mm and the supporting portion is not in contact with a periphery of the substrate.

Satoshi teaches a silicon dioxide film 14 on a silicon carbon film 10 and 12 of a jig body. Satoshi does not teach the size or the thickness of the jig body relative to any wafer that might be carried by the jig body. Thus, Satoshi cannot reasonably be considered to teach the thickness of the jig body or if the jig body is in contact with a periphery of a wafer.

Further, contrary to the assertions in the Office Action Satoshi does not teach a silicon plate-like member merely a jig body made of silicon carbide coated with silicon dioxide.

For at least the foregoing reasons, Satoshi cannot reasonably be considered to teach the combination of all of the features positively recited in claim 6.

Accordingly, reconsideration and withdrawal of the rejection of claim 6 under 35 U.S.C. §102(b) as being anticipated by Satoshi are respectfully requested.

The Office Action rejects claims 10 and 11 under 35 U.S.C. §102(b) as being anticipated by JP-A-2001-358086 to Takehiro. The cancellation of claims 10 and 11 renders this rejection moot.

The Office Action rejects claims 1-5 under 35 U.S.C. §103(a) as being unpatentable over Takehiro. This rejection is respectfully traversed.

The Office Action concedes that Takehiro does not teach the same range of thickness as that recited in claim 1. The Office Action asserts that it would have been obvious to use a supporting portion thicker than the substrate.

Takehiro teaches at, *e.g.*, paragraph [0024] a single crystal wafer 10 for installation on the support plate 11. Takehiro would not have suggested the thickness of wafer 10 or support plate 13 more than twice the thickness of single crystal wafers 1.

It is well known to one of ordinary skill that silicon wafers of smaller diameter do not need to be so thick to survive wafer-processing. Takehiro would not have suggested any especially thick wafers for use as wafer 10. Thus, one of ordinary skill would expect wafer 10 to be thinner than wafer 11.

On page 3, line 23 - page 5, line 20 of Applicants' specification the issues of using a standard thickness dummy wafer, as suggested by Takehiro are discussed. Specifically Applicants' specification discloses that thin dummy wafers suffer slip dislocations due to a difference of thermal expansion with a SiC substrate support. Further, that normal thickness

dummy wafers also suffer slip dislocations due to thermal expansion of any film on the dummy wafer. The specification further discloses in this portion, that making a support portion thick solves these specific issues. Takehiro does not address the above issues, therefore, Takehiro would not have suggested these features. Further, it would not have been predicable to use a thicker wafer 10, without the disclosure of the issues of using a standard thickness wafer provided by the Applicants' disclosure. Thus, the Office Action appears to draw its conclusions through the impermissible application of hindsight reasoning based on the road map provided by the Applicants' application.

Takehiro teaches at *e.g.* paragraph [0026] a support plate 13 with a center section 12 raised 1mm over a 150mm diameter circle made from SiC. Takehiro would not have suggested support plate 13 and center section 12 made from silicon.

For at least the foregoing reasons, Takehiro cannot reasonably be considered to have suggested the combination of all of the features recited in claim 1. Further, Takehiro cannot reasonably be considered to have suggested the combination of all of the features recited in claim 5 for at least the dependence of this claim on allowable base claims, as well as for the separately patentable subject matter that this claim recites.

Accordingly, reconsideration and withdrawal of the rejection of claims 1 and 5 under 35 U.S.C. §103(a) as being unpatentable over Takehiro are respectfully requested.

The Office Action rejects claims 7-9 under 35 U.S.C. §103(a) as being unpatentable over Satoshi. The cancellation of claims 7-9 renders this rejection moot.

The Office Action rejects claims 12 and 13 under 35 U.S.C. §103(a) as being unpatentable over Takehiro in view of Satoshi. This rejection is respectfully traversed.

The Office Action concedes that Takehiro does not teach that the uppermost film is silicon oxide. The Office Action asserts that Satoshi remedies these shortfalls of Takehiro. As argued above, Takehiro cannot reasonably be considered have suggested the combination

of all of the features recited in claim 6. Satoshi as applied to claim 6 does not remedy these shortfalls of Takehiro. Therefore, the combination of Takehiro with Satoshi cannot reasonably be considered to have suggested the combination of all of the features recited in claim 12 for at least the dependence of this claim on an allowable base claim, as well as for the separately patentable subject matter that this claim recites.

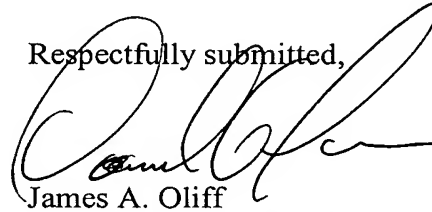
Accordingly, reconsideration and withdrawal of the rejection of claim 12 under 35 U.S.C. §103(a) as being unpatentable over Takehiro in view of Satoshi are respectfully requested.

Added claims 19-20 and dependent claim 21 are allowable at least for the inclusion of the feature discussed above with respect to, for example, claims 1 and 6 that are not disclosed in any combination of the applied references.

In view of the foregoing, it is respectfully submitted that this application is in condition for allowance. Favorable reconsideration and prompt allowance of claims 1, 5, 6, 12 and 19-21, in addition to the rejoinder of claims 15-18, are earnestly solicited.

Should the Examiner believe that anything further would be desirable in order to place this application in even better condition for allowance, the Examiner is invited to contact the undersigned at the telephone number set forth below.

Respectfully submitted,



James A. Oliff

Registration No. 27,075

Daniel A. Tanner, III

Registration No. 54,734

JAO:MIL/add

Attachment:

Petition for Extension of Time

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OLIFF & BERRIDGE, PLC
P.O. Box 320850
Alexandria, Virginia 22320-4850
Telephone: (703) 836-6400

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